

## KSD5703

### **High Voltage Color Display Horizontal Deflection Output** (No Damper Diode)

- High Collector-Base Voltage :  $V_{CBO}$ =1500V High Switching Speed  $t_F$  = 0.3 $\mu$ s (Max.)
- For Color TV



## **NPN Triple Diffused Planar Silicon Transistor**

## Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	1500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current (DC)	10	Α
I <sub>CP</sub>	Collector Current (Pulse)	30	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	70	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

## Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition Min. Typ		Тур.	Max.	Units
I <sub>CES</sub>	Collector Cut-off Current	V <sub>CE</sub> = 1400V, V <sub>BE</sub> =0			1	mA
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 800V, I_{E} = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 4V, I_{C} = 0$			1	mA
h <sub>FE1</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 1A$	15		40	
h <sub>FE2</sub>		$V_{CE} = 5V, I_{C} = 8A$	5.3		7.3	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 8A, I_B = 1.6A$			5	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A, I <sub>B</sub> = 1.6A			1.5	V
t <sub>F</sub>	Fall Time	$V_{CC} = 200V, I_{C} = 6A$		0.1	0.3	μs
		$I_{B1} = 1.2A, I_{B2} = -2.4A$				
		$R_L = 33.3\Omega$				

## **Typical Characteristics**

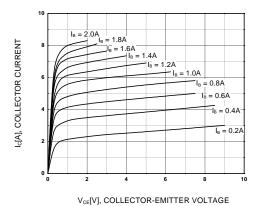


Figure 1. Static Characteristic

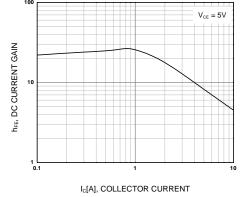


Figure 2. DC current Gain

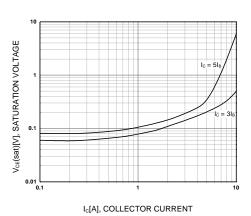


Figure 3. Collector-Emitter Saturation Voltage

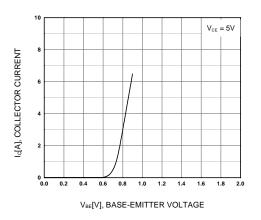


Figure 4. Base-Emitter On Voltage

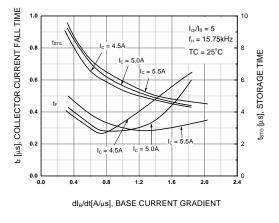


Figure 5. Switching Time

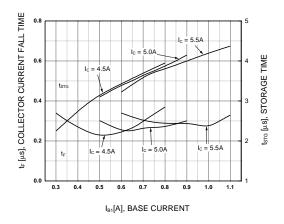
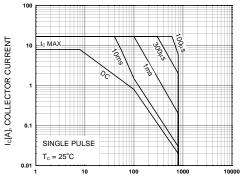


Figure 6. Switching Time

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# Typical Characteristics (Continued)



 $V_{\text{CE}}[V], \, \text{COLLECTOR-EMITTER} \, \, \text{VOLTAGE}$ 

Figure 7. Safe Operating Area

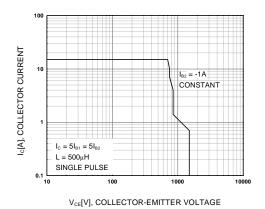


Figure 8. Reverse Bias Operating Area

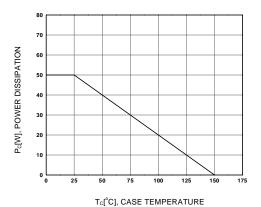
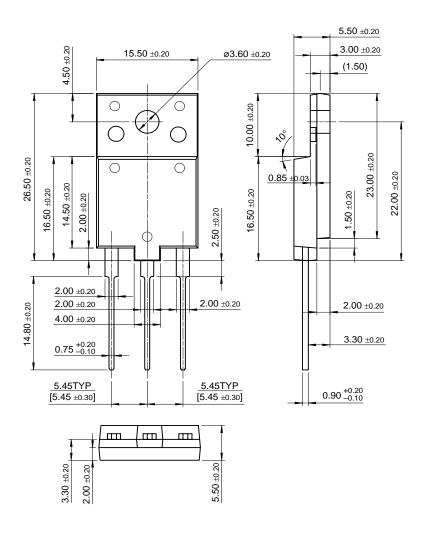


Figure 9. Power Derating

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## **Package Demensions**

## TO-3PF



Dimensions in Millimeters

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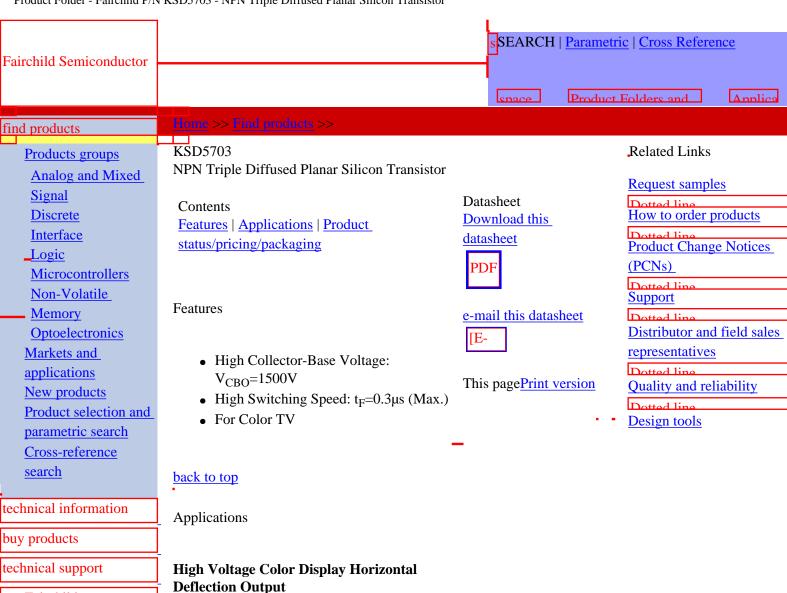
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Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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Product status/pricing/packaging

Product	<b>Product status</b>	Pricing*	Package type	Leads	Packing method
KSD5703ATBTU	Lifetime Buy	\$1.58	TO-3PF	3	RAIL
KSD5703AYDTBTU	Lifetime Buy	\$1.58	TO-3PF	3	RAIL
KSD5703TBTU	Lifetime Buy	\$1.58	TO-3PF	3	RAIL
KSD5703YDTBTU	Lifetime Buy	\$1.58	TO-3PF	3	RAIL

<sup>\* 1,000</sup> piece Budgetary Pricing

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